

100V 15A, 112mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB112M100AS-290A

Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	100 V
Average forward current	$I_{F(AV)}$	10 A
current ($t_p = 8.3$ ms, halfwave, 1 cycle)	I_{FSM}	250 A
Storage temperature range	T_{stg}	-50 to +150 °C
Maximum operating junction temperature	T_j	150 °C

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 1\text{mA}$	V_{BR}	105V	120V
Maximum forward voltage drop $I_F = 10\text{ A}$	V_F	0.72V	0.68V
	$\leq 2\%$		
Maximum reverse current $V_R = V_{RRM}$	I_R	50uA	8uA
	$\leq 2\%$		

Die Thickness *	11.4Mils
Die Size **	112 Mils
Top Metal Pad	107 Mils
Active Area	102.5Mils
Top Metal	Ag
Back Metal	AL

Note: 1 * : Also can offer device with 8 mils thickness
2 ** : Cutting street width is around 1.5 mils

Specification apply to die only. Actual performance may degrade when assembled.
does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.
Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.